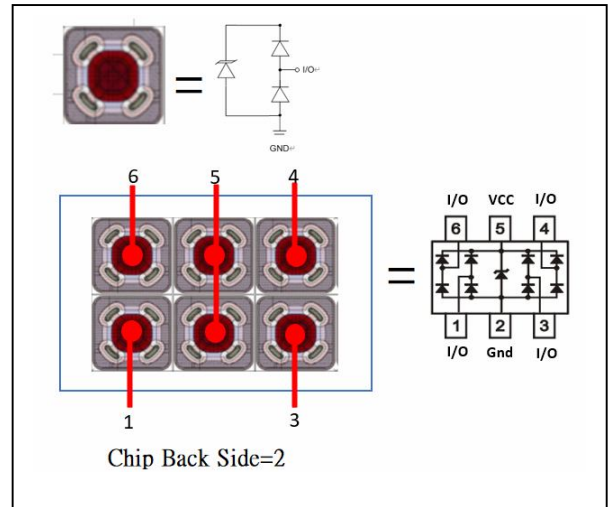


## Wafer Information

Item	Description
Wafer Size	6 inch (150mm)
Wafer Thickness	150um ± 10um
Die Size (with scribe lane)	452um x 314um
Bond Pad Opening	68um x 68um
Scribe Lane Width	40um
Gross Die Per Wafer	115,000
Top Metal (for wire bond)	4µm AlSiCu
Backside Metal (for die bond)	Ag

- Complies with IEC 61000-4-2 standards:  
Contact discharge: ±20kV

## Die Appearance



## Circuit Diagram

## Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	56	W
Peak Pulse Current (8/20µs)	IPP	4	A
Operating Temperature Range	$T_J$	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +150	$^\circ\text{C}$

## Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			5	V	
Breakdown Voltage	VBR	6			V	$I_T = 1\text{mA}$
Reverse Leakage Current	IR			100	nA	VRWM = 5V
Forward voltage	VF			1.2	V	$I_F = 15\text{mA}$
Clamping Voltage	VC			10	V	IPP = 1A (8 x 20µs pulse)
Clamping Voltage	VC			14	V	IPP = 4A (8 x 20µs pulse)
Junction Capacitance	$C_J$		0.45	0.60	pF	VR = 0V, f = 1MHz

**Note: Electrical parameters are only for die, performance may alter after assembly.**

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